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1N4148WLP-TP

Switching Diode

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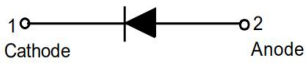
Features and benefits

- Extremely small surface mounting type.
- High Speed.

Application information

- High speed switching



DFN1006-2L

Marking: T8

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	80	V
Working Peak Reverse Voltage	V_{RWM}	80	V
DC Blocking Voltage	V_R	80	V
RMS Reverse Voltage	$V_{R(RMS)}$	57	V
Average Rectified Output Current	I_o	150	mA
Forward Current	I_{FM}	250	mA
Peak Forward Surge Current, 1μs Single Half-sine-wave	I_{FSM}	2	A
Peak Forward Surge Current, 1s Single Half-sine-wave	I_{FSM}	1	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P_D	200	mW
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	162	°C/W
Thermal Resistance Junction-to-Case *1	$R_{\theta JC}$	85	°C/W
Thermal Resistance Junction-to-Lead *1	$R_{\theta JL}$	160	°C/W
Operating Junction Temperature Range	T_J	-65 ~ +150	°C
Storage Temperature Range	T_{STG}	-65 ~ +150	°C

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	I_R = 100μA	80	-	-	V
Forward Voltage	V_F	I_F = 5mA	-	-	0.720	V
		I_F = 10mA	-	-	0.855	V
		I_F = 100mA	-	-	1.000	V
		I_F = 150mA	-	-	1.250	V
Maximum Peak Reverse Current	I_R	V_R = 20V	-	-	25	nA
		V_R = 80V	-	-	100	nA
		V_R = 25V, T_J = 125°C	-	-	30	μA
		V_R = 75V, T_J = 150°C	-	-	50	μA
Total Capacitance	C_J	V_R = 0.5V, f = 1.0MHz	-	-	3	pF
Reverse Recovery Time	t_{rr}	I_F = I_R = 10mA I_{rr} = 0.1×I_R, R_L = 100Ω	-	-	4	ns

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

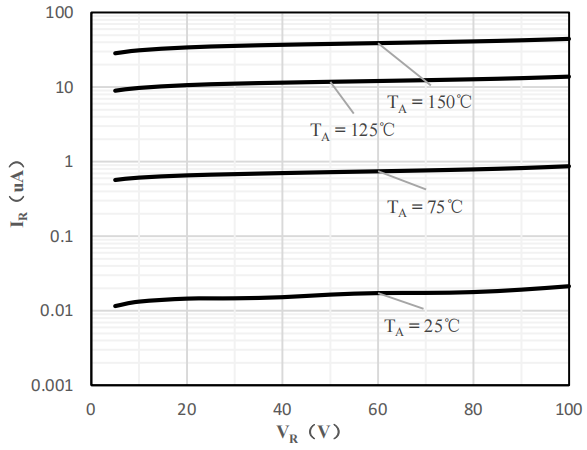


Fig 1 Typical Reverse Characteristic

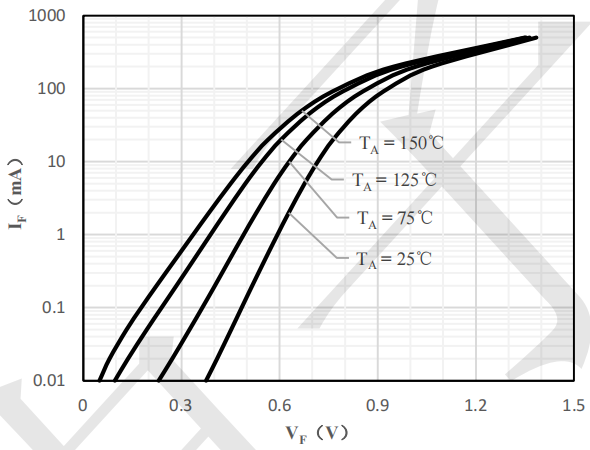


Fig 2 Typical Forward Characteristics

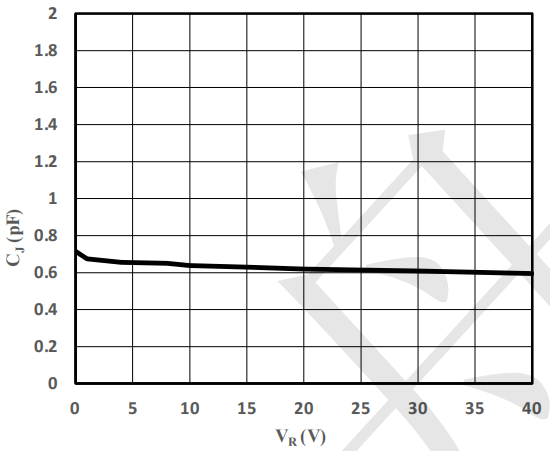


Fig 3 Capacitance vs. Reverse Voltage

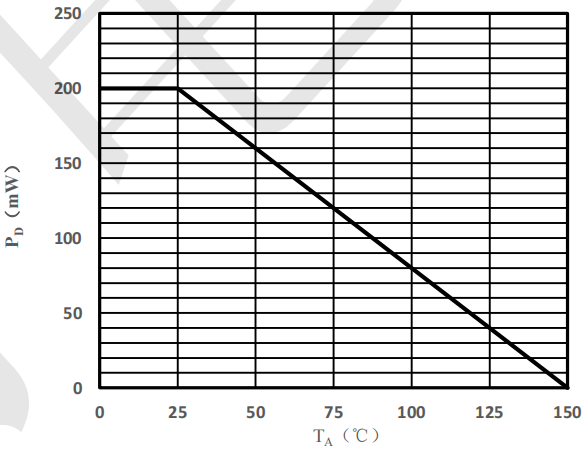
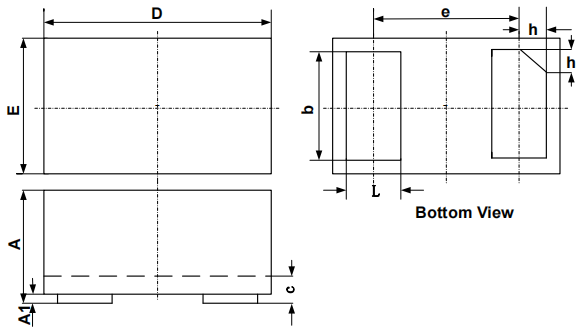


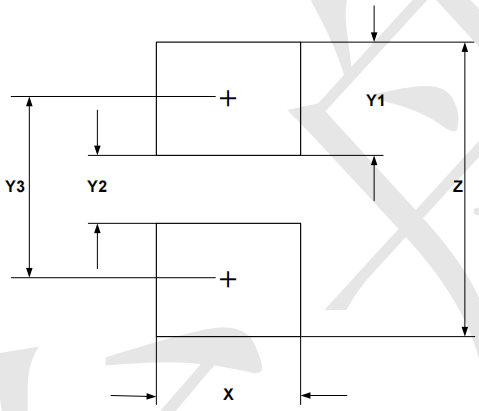
Fig 4 Power Derating Curve

Outline Drawing - DFN1006-2



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

Land Pattern - DFN1006-2



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052

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